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Form PTO-1449 U.S. DEPARTMENT OF COMMERCE ATTY. DOCKET NO. SERIAL NO. PATENT AND TRADEMARK OFFICE M122-1568 Unknown LIST OF ART CITED BY APPLICANT APPLICANT Vishnu K. Agarwal et al (Use several sheets if necessary) GROUP 2813 FILING DATE Filed Herewith U.S. PATENT DOCUMENTS Class Subclass Filing Date Date Name *Examiner Document laitial Number If Appropriate 6,232,168 5/15/2001 Coursey AB AC ΑD ΑE AF AG ΑH ΙA ΑJ ΑK FOREIGN PATENT DOCUMENTS Country Class Subclass Translation Document Date Number Yes No AM AN ΑO ΑP ΑO OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) AR

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			al "High Quality Ultra Thin SiO,N, Film Selectively Deposited on Poly-Si Electrode by LPCVD with <i>In Situ</i> HF Vapor p. 271-274 (04/1992)								
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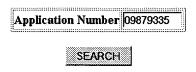
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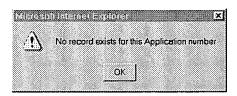
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